

PNP switching transistor

BSR18A

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- High-speed saturated switching.

DESCRIPTION

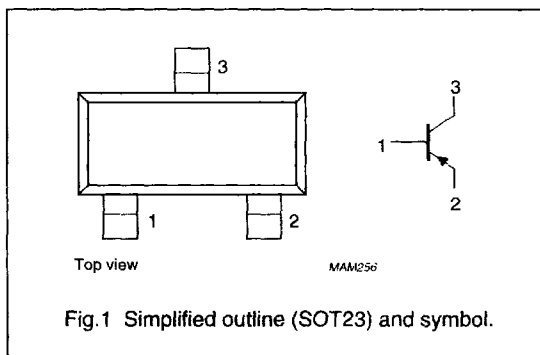
PNP switching transistor in a SOT23 plastic package.
NPN complement: BSR17A.

MARKING

TYPE NUMBER	MARKING CODE
BSR18A	T92

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–40	V
I_C	collector current (DC)		–	–100	mA
P_{Tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	250	mW
h_{FE}	DC current gain	$I_C = -10\text{ mA}$; $V_{CE} = -1\text{ V}$	100	300	
f_T	transition frequency	$I_C = -10\text{ mA}$; $V_{CE} = -20\text{ V}$; $f = 100\text{ MHz}$	250	–	MHz
t_{off}	turn-off time	$I_{Con} = -10\text{ mA}$; $I_{Bon} = -1\text{ mA}$; $I_{Boff} = 1\text{ mA}$	–	300	ns

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–40	V
V_{CEO}	collector-emitter voltage	open base	–	–40	V
V_{EBO}	emitter-base voltage	open collector	–	–6	V
I_C	collector current (DC)		–	–100	mA
I_{CM}	peak collector current		–	–200	mA
I_{BM}	peak base current		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	250	mW
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -30\text{ V}$	--	-50	nA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = -6\text{ V}$	--	-50	nA
h_{FE}	DC current gain	$V_{CE} = -1\text{ V}$; note 1; see Fig.2 $I_C = -0.1\text{ mA}$ $I_C = -1\text{ mA}$ $I_C = -10\text{ mA}$ $I_C = -50\text{ mA}$ $I_C = -100\text{ mA}$	60 80 100 60 30	-- -- 300 -- --	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}$; $I_B = -1\text{ mA}$; note 1	--	-200	mV
		$I_C = -50\text{ mA}$; $I_B = -5\text{ mA}$; note 1	--	-200	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}$; $I_B = -1\text{ mA}$; note 1	-650	-850	mV
		$I_C = -50\text{ mA}$; $I_B = -5\text{ mA}$; note 1	--	-950	mV
C_c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = -5\text{ V}$; $f = 1\text{ MHz}$	--	4.5	pF
C_e	emitter capacitance	$I_C = i_c = 0$; $V_{EB} = -500\text{ mV}$; $f = 1\text{ MHz}$	--	10	pF
f_T	transition frequency	$I_C = -10\text{ mA}$; $V_{CE} = -20\text{ V}$; $f = 100\text{ MHz}$	250	--	MHz
F	noise figure	$I_C = -100\text{ }\mu\text{A}$; $V_{CE} = -5\text{ V}$; $R_S = 1\text{ k}\Omega$; $f = 10\text{ Hz to }15.7\text{ kHz}$	--	4	dB
Switching times (between 10% and 90% levels); see Fig.3					
t_{on}	turn-on time	$I_{Con} = -10\text{ mA}$; $I_{Bon} = -1\text{ mA}$; $I_{Boff} = 1\text{ mA}$	--	65	ns
t_d	delay time		--	35	ns
t_r	rise time		--	35	ns
t_{off}	turn-off time		--	300	ns
t_s	storage time		--	225	ns
t_f	fall time		--	75	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.01$.

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